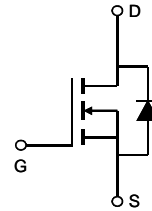
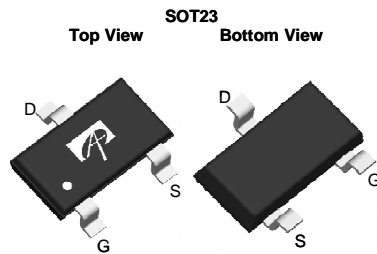


General Description

The AO3400 combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is suitable for use as a load switch or in PWM applications.

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	5.8A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 28m Ω
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	< 33m Ω
$R_{DS(ON)}$ (at $V_{GS} = 2.5V$)	< 52m Ω



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	$T_A=25^\circ\text{C}$	5.8
		$T_A=70^\circ\text{C}$	4.9
Pulsed Drain Current ^C	I_{DM}	30	A
Power Dissipation ^B	P_D	$T_A=25^\circ\text{C}$	1.4
		$T_A=70^\circ\text{C}$	0.9
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	70	90	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Ambient ^{A,D}		Steady-State	100	125
Maximum Junction-to-Lead	$R_{\theta JL}$	63	80	$^\circ\text{C}/\text{W}$